

Electronic Information Disclosure Statement

DRAM CELL WITH ENHANCED SER IMMUNITY

JC474 U.S. PTO
10/064869
08/26/02
#2

Application:

Confirmation:

Applicant(s): Jeffrey Brown

Docket
Number: BUR920010223










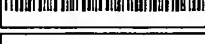







Group Art Unit:

Examiner:

search string: (4103342 or 4686552 or 4927779 or 5134616 or 5567962 or 5606189 or 5780335 or 6101117 or 6246083).pn.

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Citation No.	Patent Number	Date	Bar Code	Patentee	Class	Subclass
	P01	4103342	1978-07-25		Miersch et al.	365	149
	P02	4686552	1987-08-11		Teng et al.	357	23.6
	P03	4927779	1990-05-22		Dhong et al.	428	52
	P04	5134616	1992-07-28		Barth Jr et al.	371	10.3
	P05	5567962	1996-10-22		Miyawaki et al.	257	296
	P06	5606189	1997-02-25		Adan	257	303
	P07	5780335	1998-07-14		Henkels et al.	438	243
	P08	6101117	2000-08-08		Tiwari	365	145
							

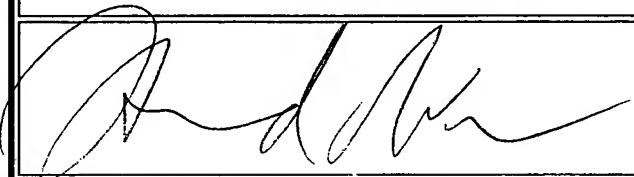
P09	6246083	2001-06-12	Noble	257	296
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Remarks

(Remarks are not for responding to an office action.)

1. FR2595160, Inventor: Kowalski, Filed 09/04/1987; 2. IBM Technical Disclosure Bulletin, Vol 31, No. 7, December 1988, pp. 409-417; 3. Hisamoto et al., "A Fully Depleted Lean-Channel Transistor (DELTA)", CH2637-7/89/0000-0833, 1989 IEEE, IEDM 89-833-836; 4. Choi et al., "Ultra-thin Body SOI MOSFET for Deep-sub-tenth Micron Era", 0-7803-5410-9/99, 1999 IEEE, IEDM 99-919-921.

Signature

Examiner Name	Date
	2/28/03